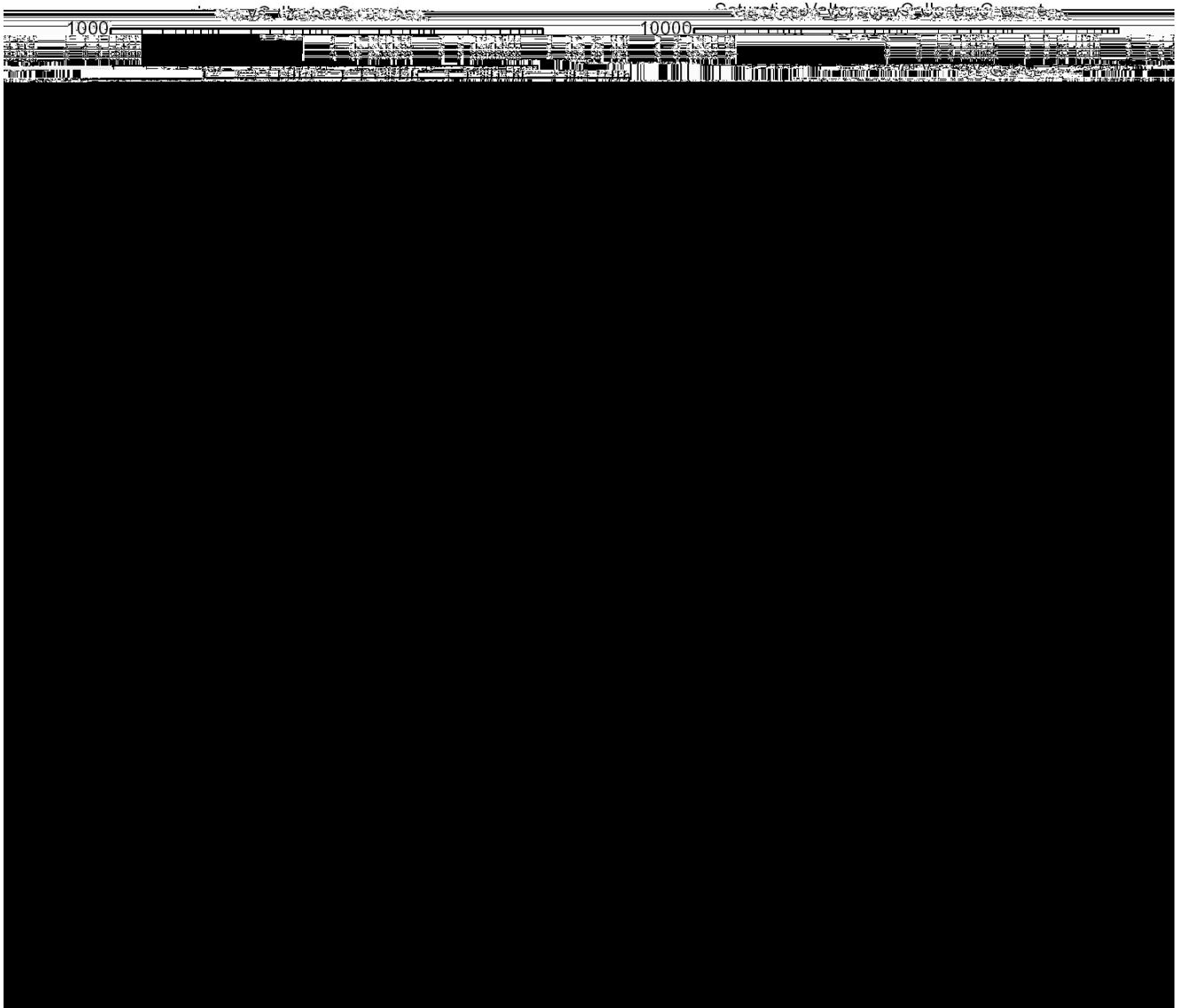


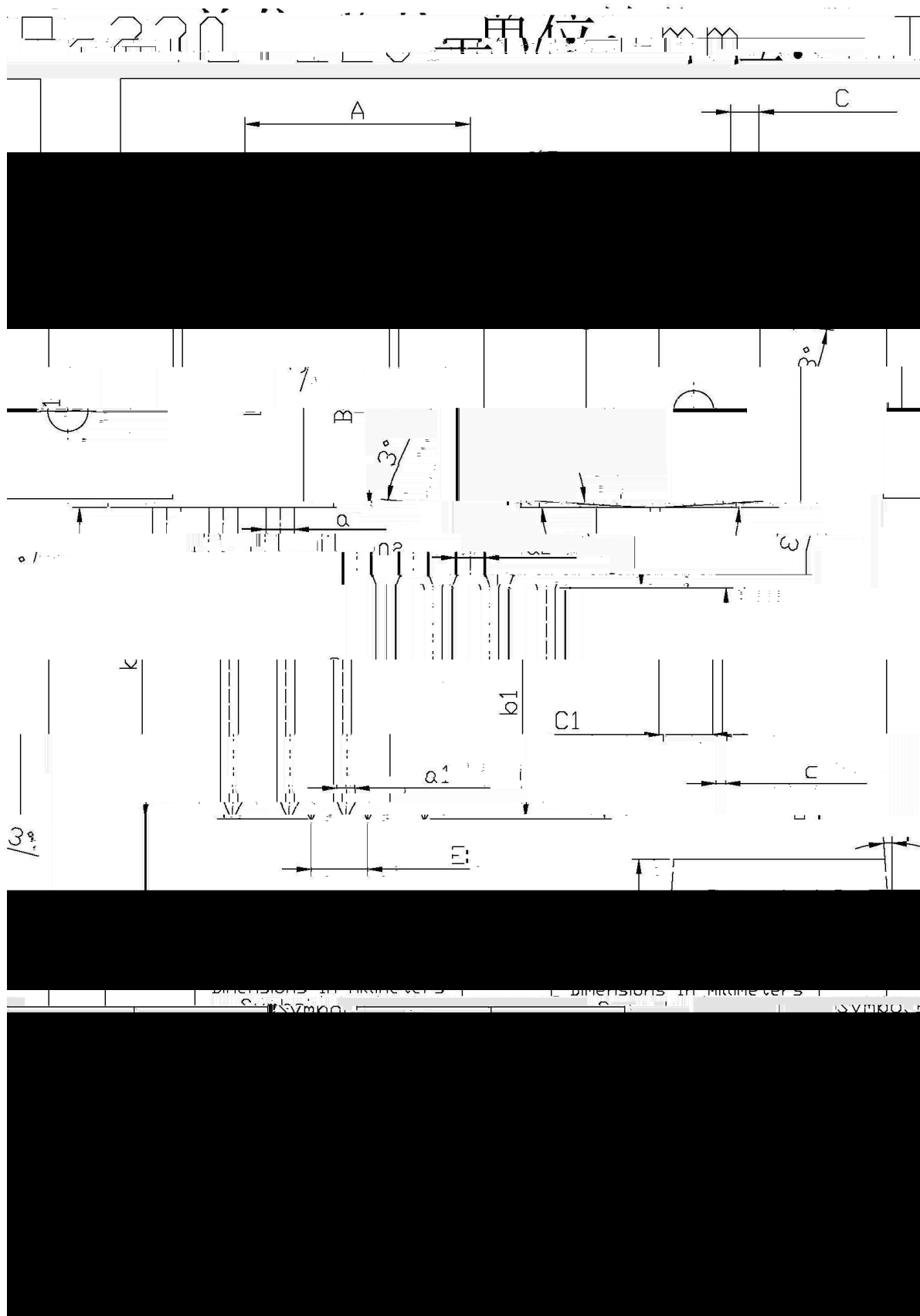
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-70	V
Collector to Emitter Voltage	V_{CEO}	-50	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-4.0	A
Base Current - Continuous	I_{CP}	-8.0	A
Collector Power Dissipation	$P_C(T_C=25^\circ C)$	40	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-10\mu A$ $I_E=0$	-70			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-50mA$ $I_B=0$	-50			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-10\mu A$ $I_C=0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-50V$ $I_E=0$			-1.0	μA
DC Current Gain	$h_{FE(1)*}$	$V_{CE}=-4.0V$ $I_C=-1.0A^*$	60		320	
	$h_{FE(2)*}$	$V_{CE}=-4.0V$ $I_C=-0.1A^*$	35			
Collector to Emitter Saturation Voltage*	$V_{CE(sat)*}$	$I_C=-2.0A$ $I_B=-0.2A^*$			-1.0	V
Base to Emitter Voltage*	V_{BE*}	$V_{CE}=-4.0V$ $I_C=-1.0A^*$			-1.0	V
Transition Frequency*	f_T^*	$V_{CE}=-4.0V$ $I_C=-0.5A^*$				

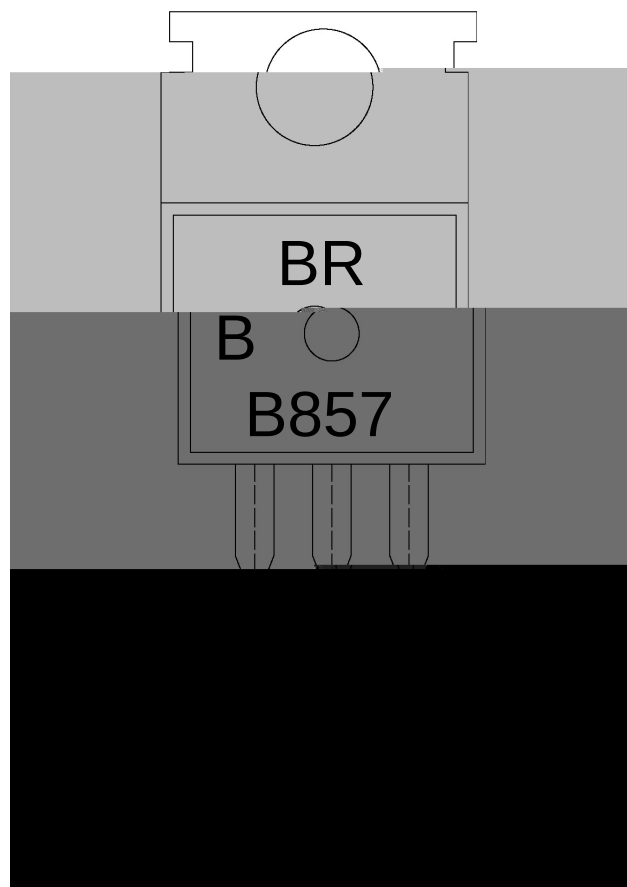
/ **Electrical Characteristic Curve**



/ Package Dimensions



/ Marking Instructions



Б " X

EU X

E; 8: X

E=

---- X

Note:

BR:

B857:

B:

****:

Б 3 " П

Б 3 " П

Б k_И " П

Б 1 f " П 1 f " П

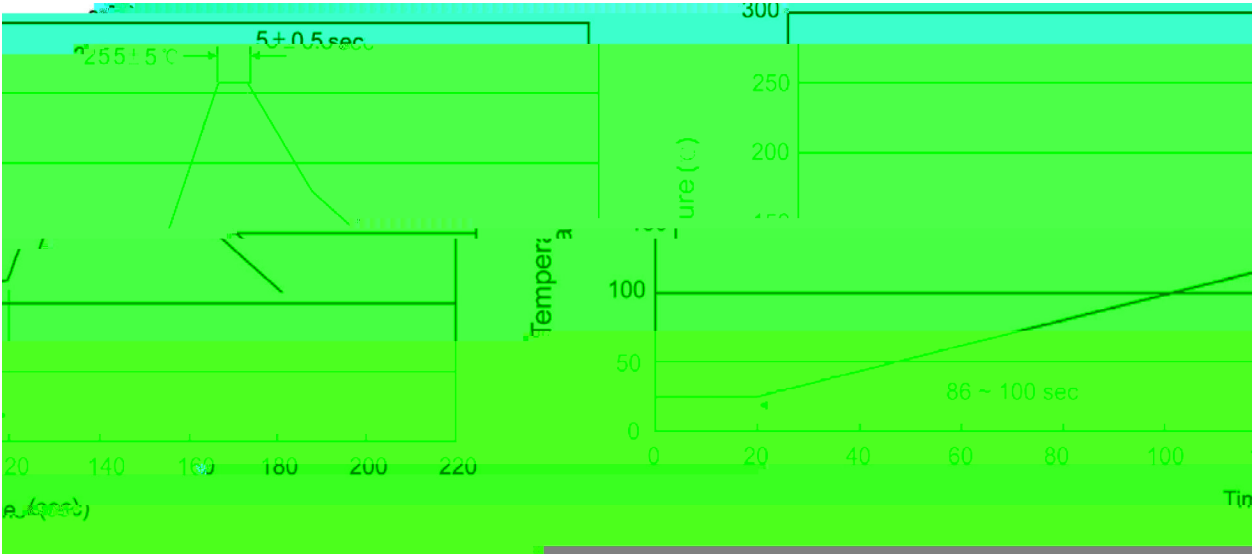
Company Code

Product Type.

h_{FE} Classifications Symbol

Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



- 说明

 1. 预加热: 25~150 °C, 时间: 60~90sec;
 2. 峰值温度: 255±5 °C, 持续时间: 5±0.5sec;
 3. 冷却速度: 2~10 °C/sec.
- Note:

 - 1.Preheating:25~150 °C , Time:60~90sec.
 - 2.Peak Temp.:255±5 °C , Duration:5±0.5sec.
 3. Cooling Speed: 2~10 °C/sec.

/ Resistance to Soldering Heat Test Conditions

温度: 270±5 °C 时间: 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

包装形式 / BULK

Package Type 封装形式	Units 包装数量		Dimension 包装尺寸 (unit: mm ³)
只袋	袋盒	只盒	